

Product Summary

V_{DS}	1200 V
$I_D (T_C=25^\circ\text{C})$	86 A
$R_{DS(on).typ}$	32 m Ω @ $V_{GS}=18\text{V}$

Features

- Low On-Resistance with High Blocking Voltage
- Low Capacitance
- Avalanche Ruggedness
- Halogen Free, Rohs Compliant

Benefits

- High Frequency Operation
- Enabling Higher Switching Frequency
- Increased Power Density
- Reduction of Heat Sink Requirements

Applications

- Switch Mode Power Supplies (SMPS)
- Power Inverter & Solar Inverter
- Motor Drivers & EV Charging Station
- DC/DC Converter

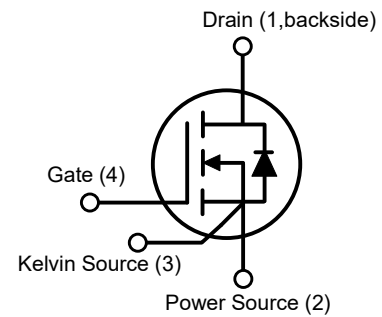
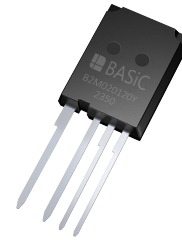
Package Pin Definitions

- Pin1 and backside - Drain
- Pin2 - Power Source
- Pin3 - Kelvin Source
- Pin4 - Gate

Package Parameters

Part Number	Marking	Package
B2M032120Y	B2M032120Y	TO-247PLUS-4

Package: TO-247PLUS-4



Maximum Ratings

Symbol	Parameter	Test conditions	Value	Unit
V_{DSmax}	Drain-Source Voltage	$V_{GS}=0V, I_D=100\mu A$	1200	V
$V_{GSmax}^{1)}$	Gate-Source Voltage		-8/22	V
V_{GSop}	Recommend Gate-Source Voltage		-4/18	V
I_D	Continuous Drain Current	$V_{GS}=18V, T_C=25^\circ C$	86	A
		$V_{GS}=18V, T_C=100^\circ C$	60	A
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	190	A
P_{tot}	Power Dissipation	$T_C=25^\circ C, T_j=175^\circ C$	375	W
T_j	Operating Junction Temperature		-55~175	$^\circ C$
T_{stg}	Storage Temperature		-55~175	$^\circ C$

1) Note: When using MOSFET Body Diode $V_{GSmax} = -4/22V$

Electrical Characteristics (Defined at $T_j=25^\circ C$ unless otherwise specified)
Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=100\mu A$	1200			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=10mA$	2.3	2.8	3.5	V
		$V_{GS}=V_{DS}, I_D=10mA, T_j=175^\circ C$		1.9		
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=18V, V_{DS}=0V$			100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=1200V, V_{GS}=0V$		1	50	μA
		$V_{DS}=1200V, V_{GS}=0V, T_j=175^\circ C$		10	200	
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=18V, I_D=40A$		32	50	m Ω
		$V_{GS}=18V, I_D=40A, T_j=175^\circ C$		50		
g_{fs}	Transconductance	$V_{DS}=10V, I_D=40A$		18		S

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal Resistance from Junction to Case		0.40		K/W

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=800V$ $f=100KHz, V_{AC}=25mV$		2700		pF
C_{oss}	Output Capacitance			150		pF
C_{rss}	Reverse Transfer Capacitance			7		pF
$R_{G(int)}$	Internal Gate Resistance	$f=1MHz, V_{AC}=25mV$		1.2		Ω

Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_{GS}	Gate to Source Charge	$V_{DS} = 800V$ $I_D = 40A$ $V_{GS} = -4/+18V$		40		nC
Q_{GD}	Gate to Drain Charge			57		nC
Q_G	Total Gate Charge			115		nC

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$t_{d(on)}$	Turn-On Delay Time	$V_{DC}=800V, V_{GS}=-4/18V$ $I_D=40A, R_{G(ext)}=4.7\Omega$ $L_\sigma=70nH, T_j=25^\circ C$ diode: body diode at $V_{GS}=-4V$ Inductive Load Eon includes diode reverse recovery		8		ns
t_r	Rise Time			29		ns
$t_{d(off)}$	Turn-Off Delay Time			25		ns
t_f	Fall Time			13		ns
E_{on}	Turn-On Energy			518		uJ
E_{off}	Turn-Off Energy			201		uJ
$t_{d(on)}$	Turn-On Delay Time	$V_{DC}=800V, V_{GS}=-4/18V$ $I_D=40A, R_{G(ext)}=4.7\Omega$ $L_\sigma=70nH, T_j=175^\circ C$ diode: body diode at $V_{GS}=-4V$ Inductive Load Eon includes diode reverse recovery		6		ns
t_r	Rise Time			31		ns
$t_{d(off)}$	Turn-Off Delay Time			29		ns
t_f	Fall Time			12		ns
E_{on}	Turn-On Energy			702		uJ
E_{off}	Turn-Off Energy			171		uJ

Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{SD}	Diode Forward Voltage	$V_{GS}=-4V, I_{SD}=20A, T_j=25^\circ C$		4.4		V
		$V_{GS}=-4V, I_{SD}=20A, T_j=175^\circ C$		3.7		
I_{SD}	Continuous Diode Forward Current	$V_{GS}=-4V, T_C=25^\circ C$			68	A
$I_{SD,pulse}$	Pulse Diode Current	$V_{GS}=-4V$, pulse width t_p limited by T_{jmax}		170		A
t_{rr}	Reverse Recovery Time	$V_{DC}=800V, I_{SD}=40A$ $-di_F/dt=2800A/\mu s$ $T_j=25^\circ C$		16		ns
Q_{rr}	Reverse Recovery Charge			206		nC
I_{rrm}	Peak Reverse Recovery Current			21		A
t_{rr}	Reverse Recovery Time	$V_{DC}=800V, I_{SD}=40A$ $-di_F/dt=3600A/\mu s$ $T_j=175^\circ C$		26		ns
Q_{rr}	Reverse Recovery Charge			959		nC
I_{rrm}	Peak Reverse Recovery Current			60		A

Typical Performance

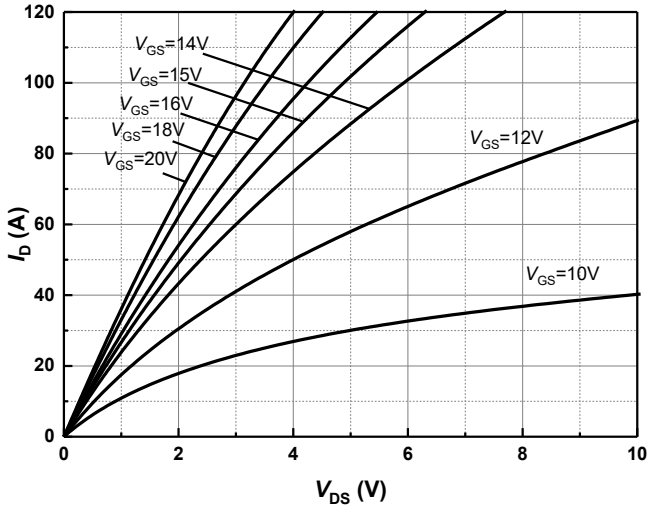


Figure 1 Typical Forward Output Characteristics at $T_j = 25^\circ\text{C}$

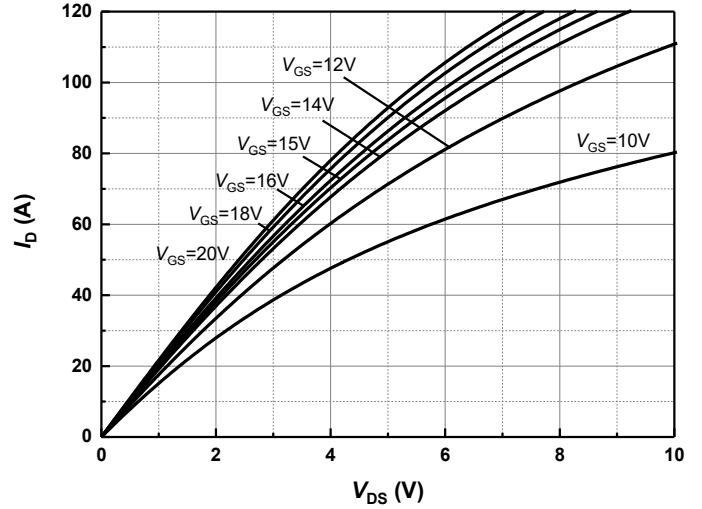


Figure 2 Typical Forward Output Characteristics at $T_j = 175^\circ\text{C}$

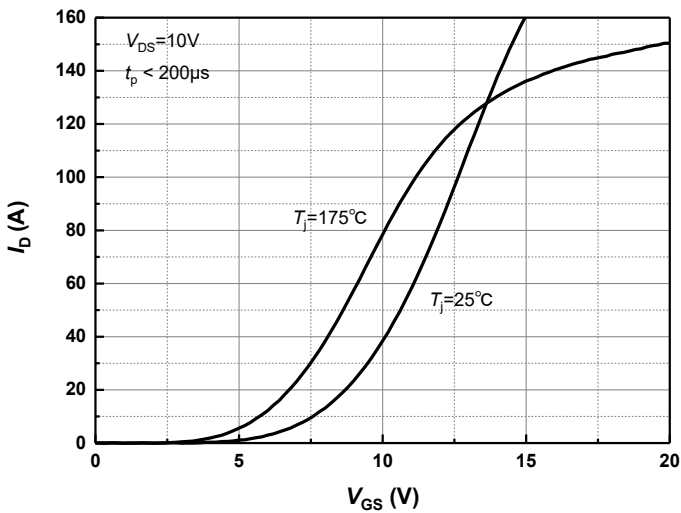


Figure 3 Transfer Characteristics for Various Temperature

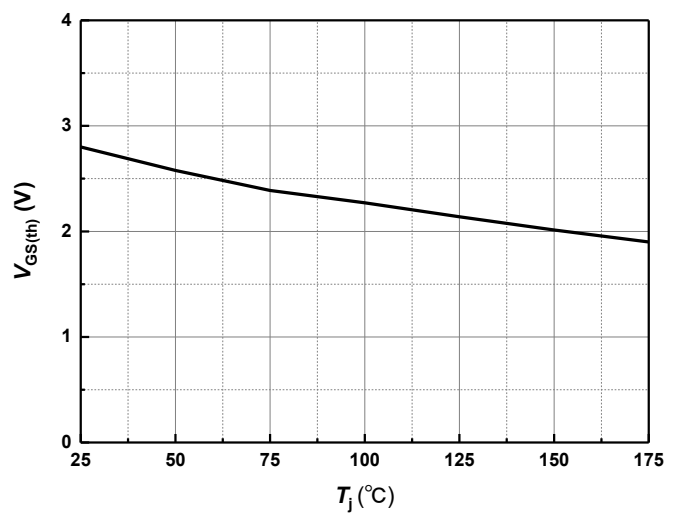


Figure 4 Threshold Voltage for Various Temperature

Typical Performance

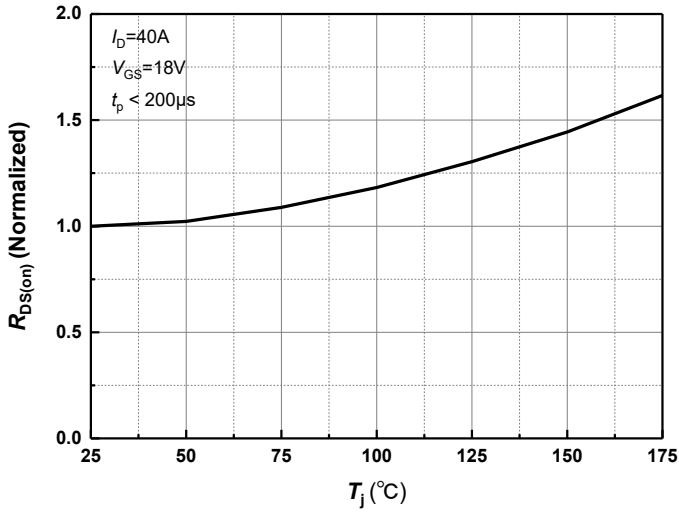


Figure 5 Normalized On-Resistance for Various Temperature

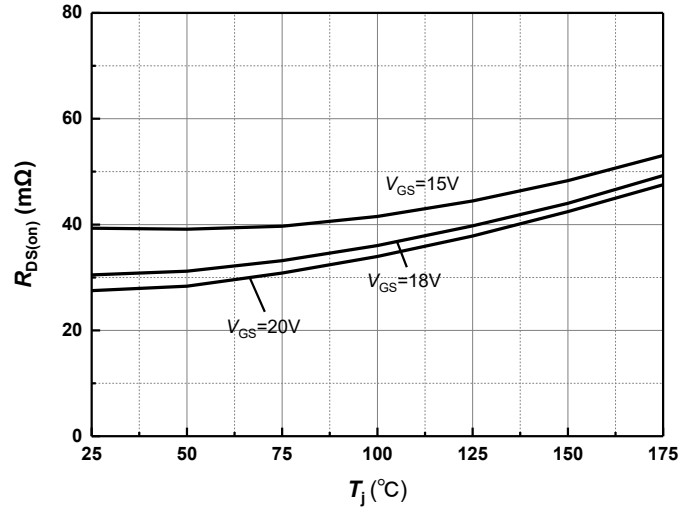


Figure 6 On-Resistance vs. Temperature for Various Gate-Source Voltage

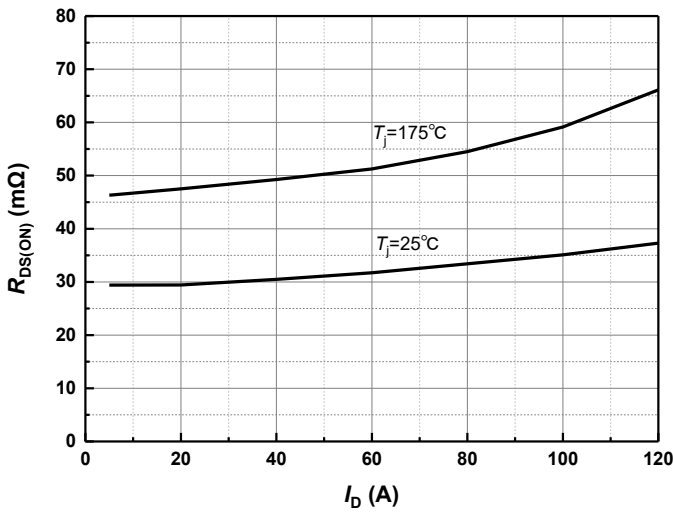


Figure 7 On-Resistance vs. Drain Current for Various Temperature

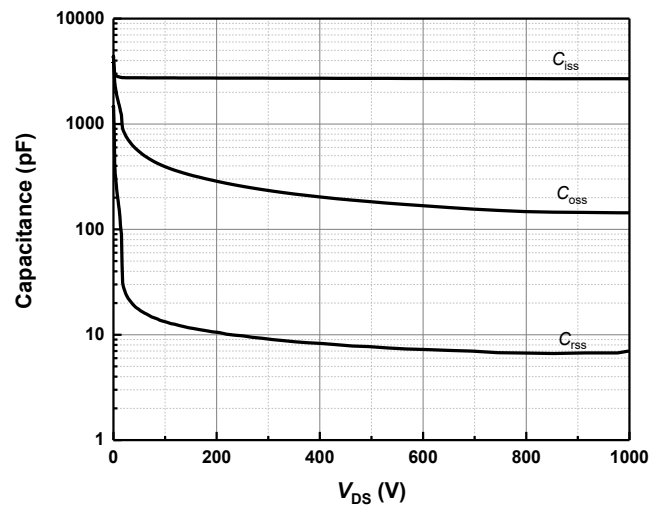


Figure 8 Capacitance vs. Drain-Source Voltage (0 - 1000V)

Typical Performance

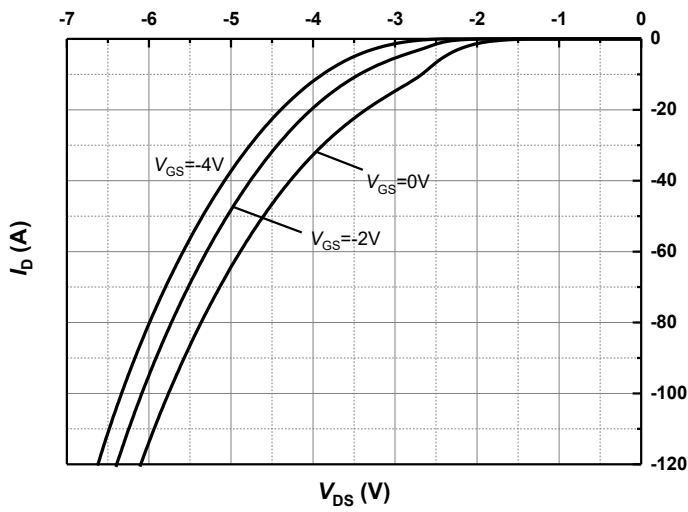


Figure 9 Body Diode Characteristics at $T_j=25^\circ\text{C}$

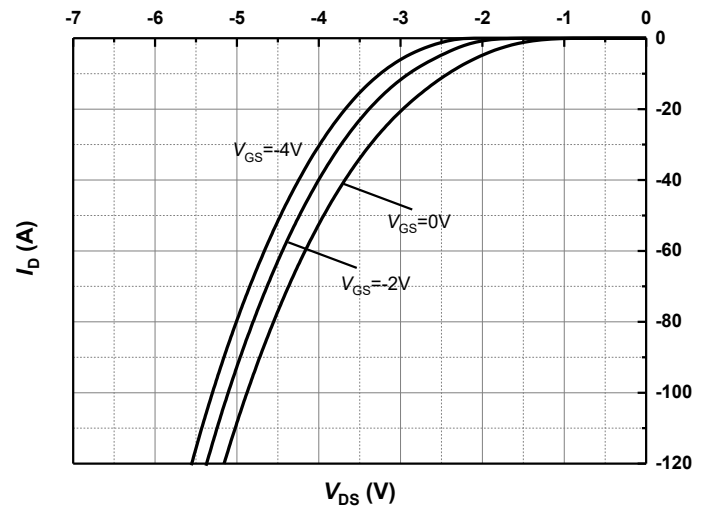


Figure 10 Body Diode Characteristics at $T_j=175^\circ\text{C}$

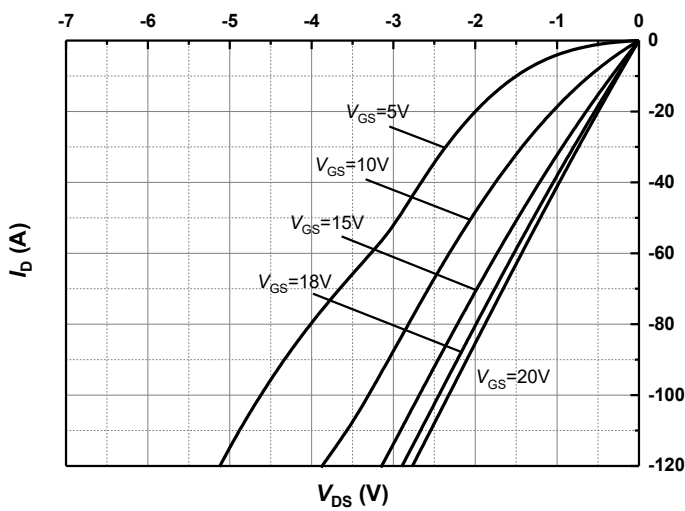


Figure 11 3rd Quadrant Characteristics at $T_j=25^\circ\text{C}$

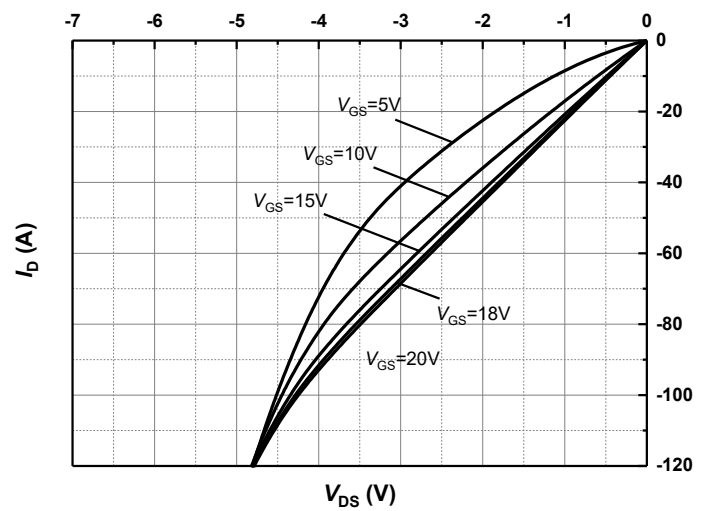


Figure 12 3rd Quadrant Characteristics at $T_j=175^\circ\text{C}$

Typical Performance

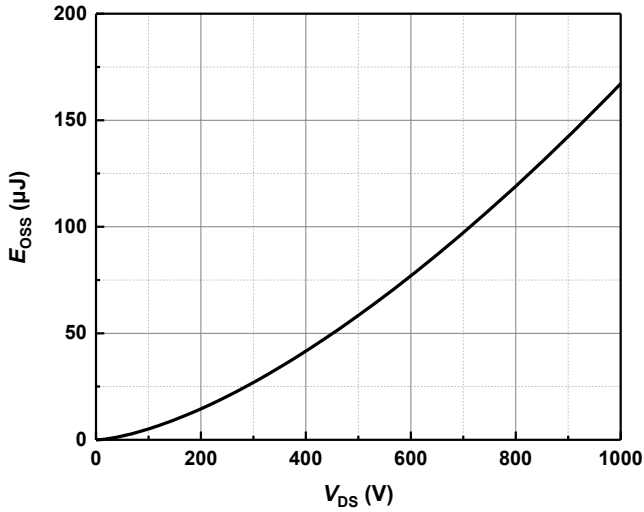


Figure 13 Output Capacitor stored Energy

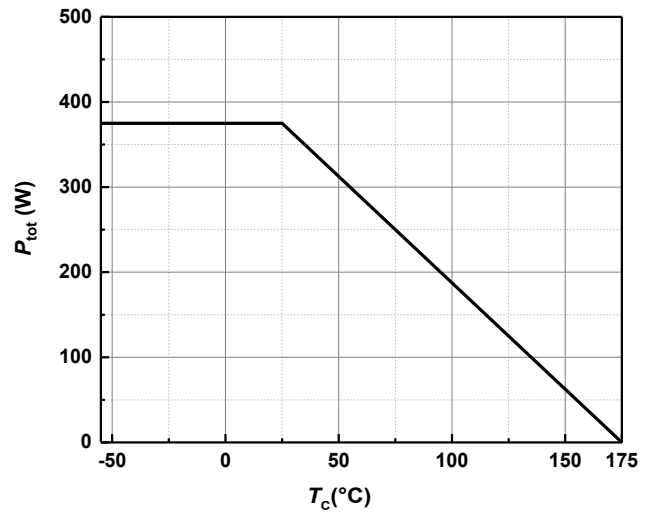


Figure 14 Maximum Power Dissipation Derating vs. Case Temperature

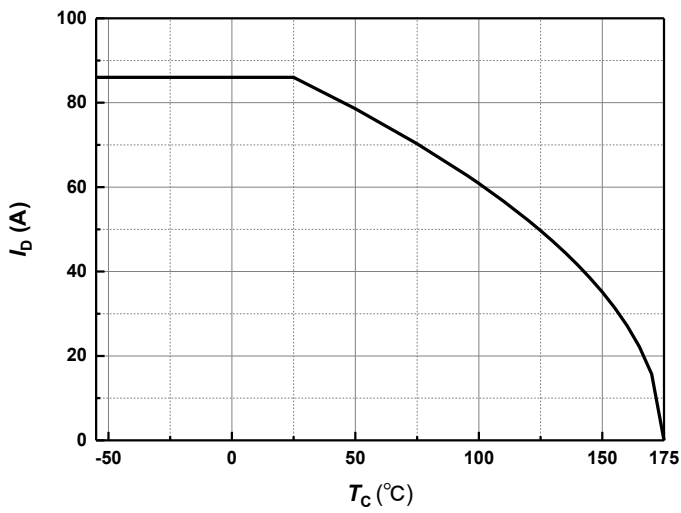


Figure 15 Continuous Drain Current Derating vs. Case Temperature

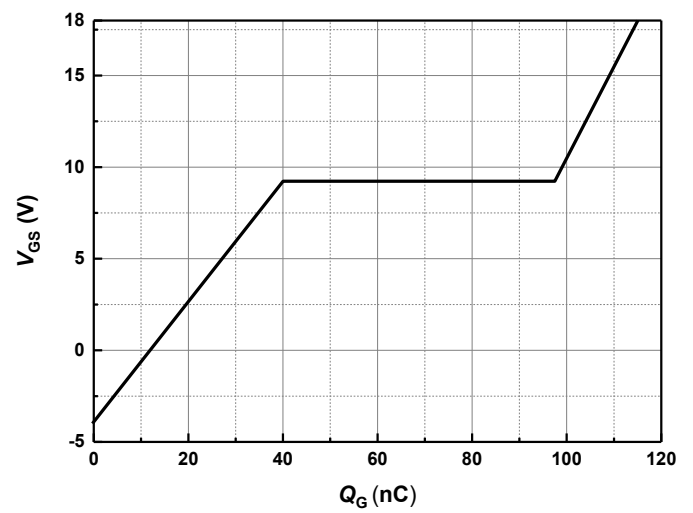


Figure 16 Gate Charge Characteristics

Typical Performance

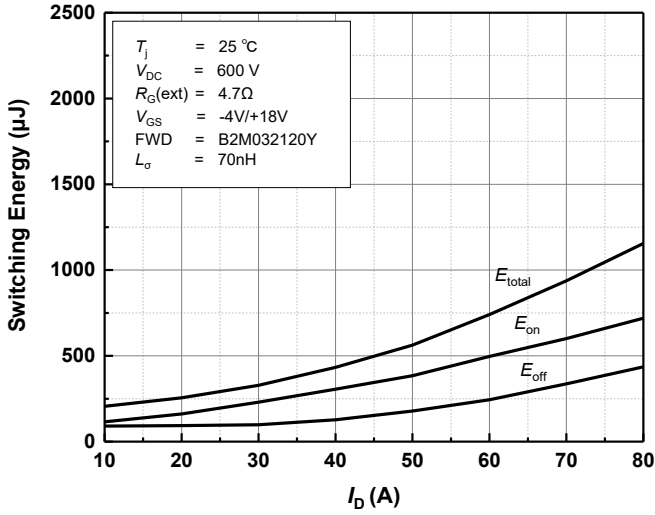


Figure 17 Clamped Inductive Switching Energy vs. Drain Current ($V_{DC} = 600\text{V}$) at $T_j = 25^\circ\text{C}$

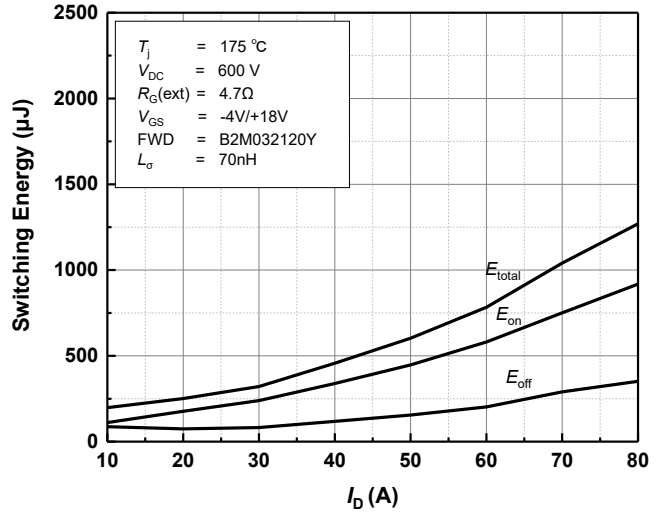


Figure 18 Clamped Inductive Switching Energy vs. Drain Current ($V_{DC} = 600\text{V}$) at $T_j = 175^\circ\text{C}$

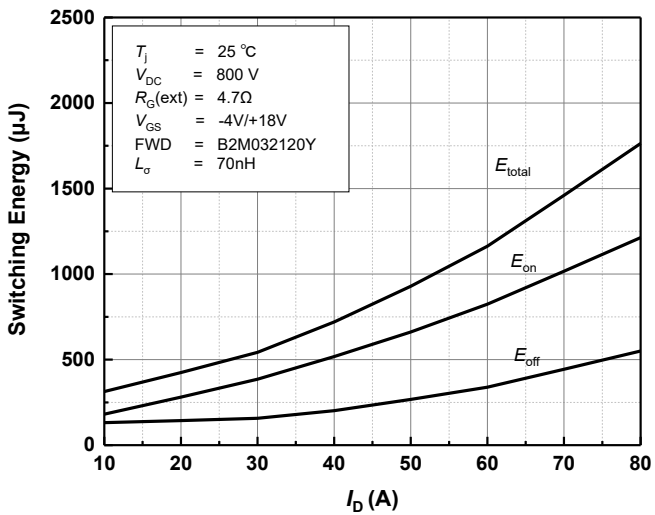


Figure 19 Clamped Inductive Switching Energy vs. Drain Current ($V_{DC} = 800\text{V}$) at $T_j = 25^\circ\text{C}$

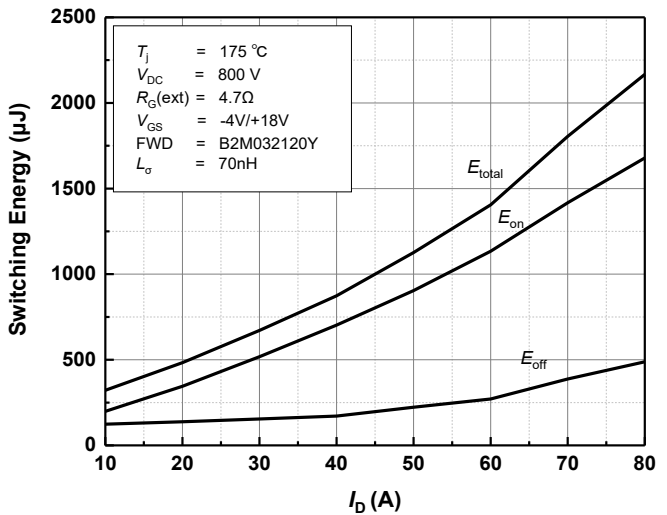


Figure 20 Clamped Inductive Switching Energy vs. Drain Current ($V_{DC} = 800\text{V}$) at $T_j = 175^\circ\text{C}$

Typical Performance

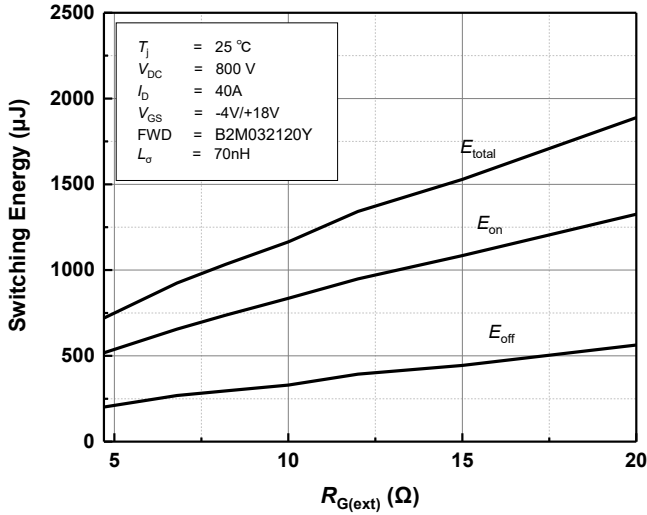


Figure 21 Clamped Inductive Switching Energy vs. External Gate Resistance at $T_j=25^\circ\text{C}$

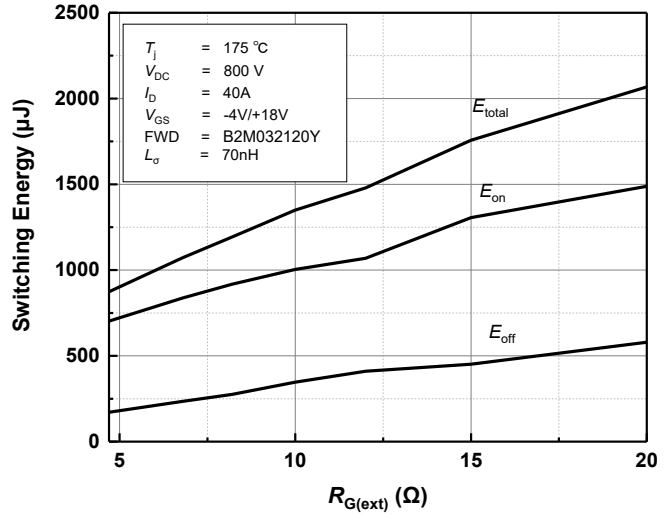


Figure 22 Clamped Inductive Switching Time vs. External Gate Resistance at $T_j=175^\circ\text{C}$

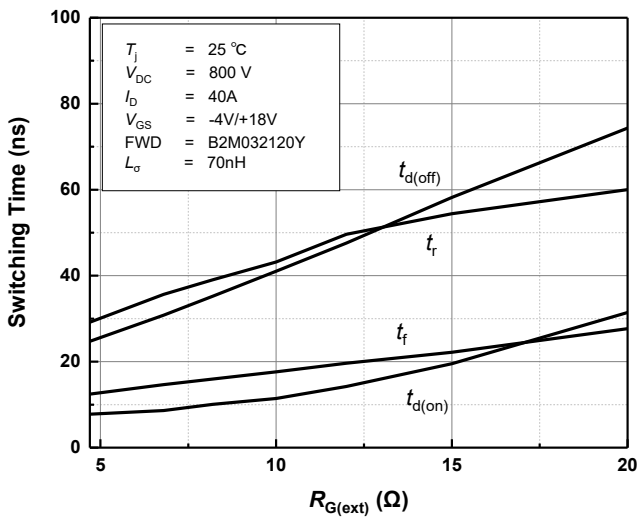


Figure 23 Clamped Inductive Switching Time vs. External Gate Resistance at $T_j=25^\circ\text{C}$

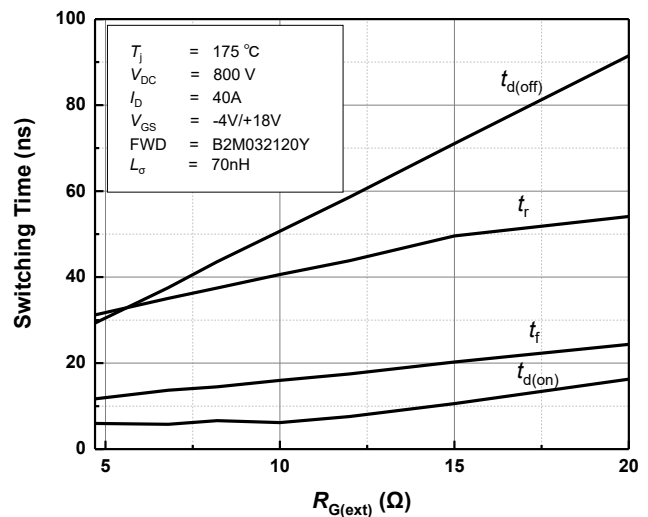


Figure 24 Clamped Inductive Switching Time vs. External Gate Resistance at $T_j=175^\circ\text{C}$

Typical Performance

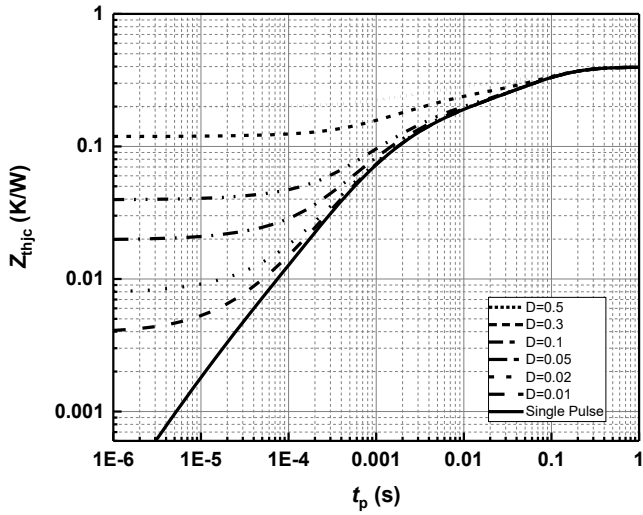


Figure 25 Transient Thermal Impedance (Junction - Case)

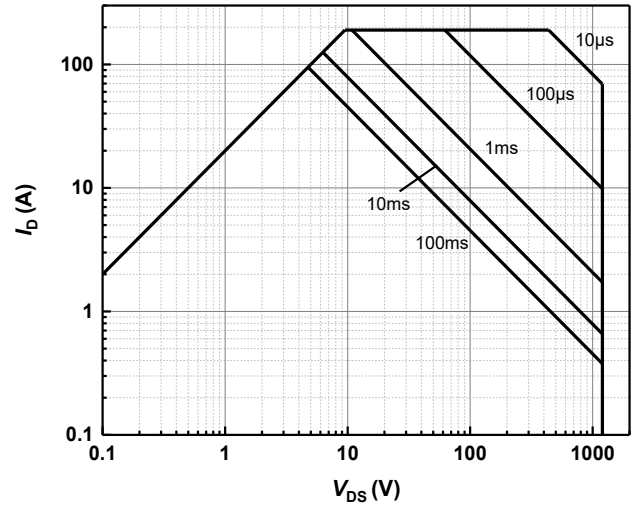
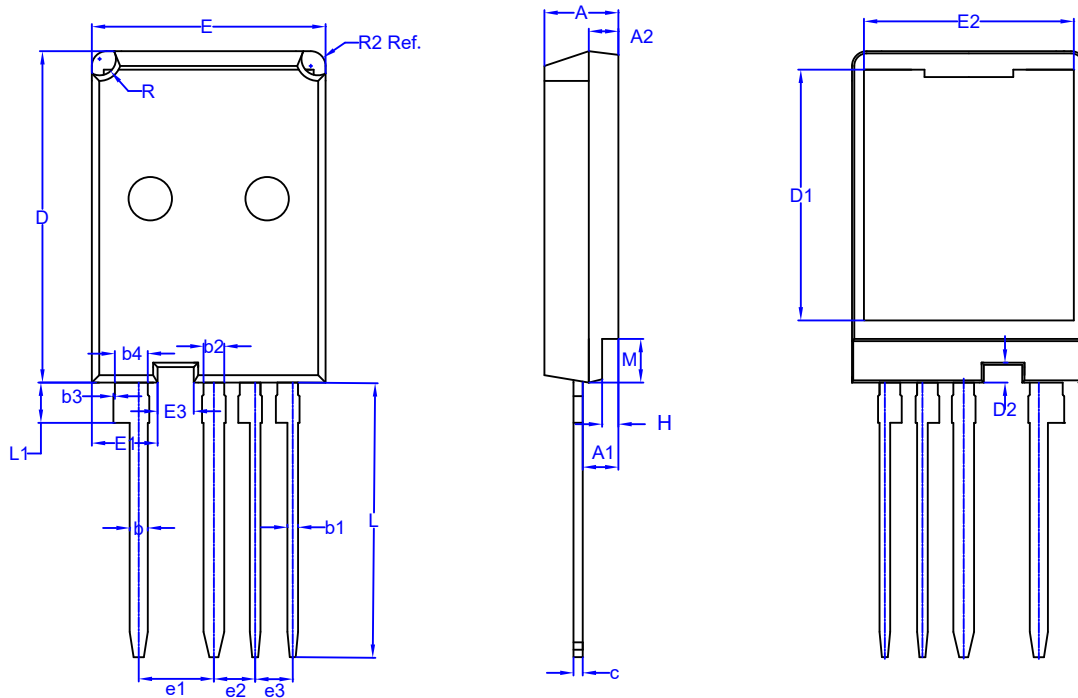


Figure 26 Forward Biased Safe Operating Area

Package Dimensions



SYMBOL	mm		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.80	2.00	2.20
b	1.15	1.25	1.35
b1	0.60	0.70	0.80
b2	1.32	1.42	1.52
b3	0.00	0.10	0.20
b4	2.12	2.22	2.32
c	0.50	0.60	0.70
D	22.2	22.4	22.6
D1	16.6	17.0	17.25
D2	0.95	1.10	1.25
E	15.6	15.8	16.0
E1	3.90	4.0	4.10
E2	13.1	13.3	13.50
E3	2.58	2.68	2.78
e1	5.080BSC		
e2	2.790BSC		
e3	2.540BSC		
H	1.00	1.10	1.20
L	18.36	18.56	18.76
L1	2.62	2.72	2.82
M	2.85	2.95	3.05
R	1.90	2.00	2.10

Revision History

Document Version	Date of Release	Description of Changes
Rev. 0.0	2023-06-09	Draft datasheet created.

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